

Claims

1-4."canceled".

5."new". A transistor comprising on both sides of a lightly doped silicon monocrystal substrate having a donor concentration of about 10^{14} cm.⁻³:
an epitaxial layer having a donor concentration of about 10^{17} cm.⁻³,
wherein elements of a bipolar static induction transistor: a p⁺ gate, n⁺ sources and n-channels are disposed;

one channel of a multielement structure is thicker than the other normally-off channels.

6."new". The transistor according to claim 5 wherein a layer of a doped n⁺ type polysilicon is disposed on the silicon monocrystal surface on both sides of said substrate.

7."new". A transistor comprising on both sides of a lightly doped silicon monocrystal substrate having a donor concentration of about 10^{14} cm.⁻³:
an epitaxial layer having a donor concentration of about 10^{17} cm.⁻³,
wherein elements of a bipolar static induction transistor: a p⁺ gate, n⁺ sources and n-channels are disposed;

one channel of a multielement structure is thicker than the other normally-off channels;

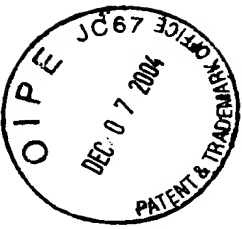
said channel is connected to a separate electrode.

8."new". The transistor according to claim 7 wherein a layer of a doped n⁺ type polysilicon is disposed on the silicon monocrystal surface on both sides of said substrate.

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Claims

1-4."canceled".

5."new". A transistor comprising on both sides of a lightly doped silicon monocrystal substrate having a donor concentration of about 10^{14} cm.^{sup.}-3: an epitaxial layer having a donor concentration of about 10^{17} cm.^{sup.}-3, wherein elements of a bipolar static induction transistor: a p⁺ gate, n⁺ sources and n-channels are disposed;

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6."new. The transistor according to claim 5 wherein a layer of a doped n⁺ type polysilicon is disposed on the silicon monocrystal surface on both sides of said substrate.

7."new". A transistor comprising on both sides of a lightly doped silicon monocrystal substrate having a donor concentration of about 10^{14} cm.^{sup.}-3: an epitaxial layer having a donor concentration of about 10^{17} cm.^{sup.}-3, wherein elements of a bipolar static induction transistor: a p⁺ gate, n⁺ sources and n-channels are disposed;

one channel of a multielement structure is thicker than the other normally-off channels;

said channel is connected to a separate electrode.

8."new. The transistor according to claim 7 wherein a layer of a doped n⁺ type polysilicon is disposed on the silicon monocrystal surface on both sides of said substrate.

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